

isc Silicon NPN Darlington Power Transistor

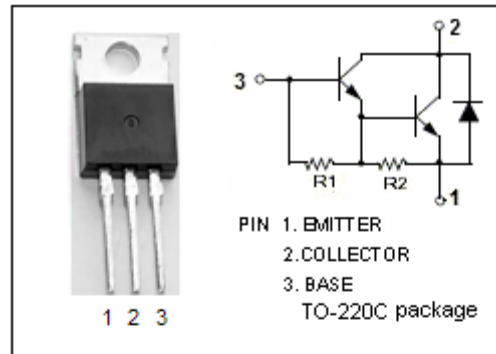
MJE800T

DESCRIPTION

- Collector–Emitter Breakdown Voltage—  
:  $V_{(BR)CEO} = 60\text{ V}$
- DC Current Gain—  
:  $h_{FE} = 750(\text{Min}) @ I_C = 2\text{ A}$
- Complement to Type MJE700T

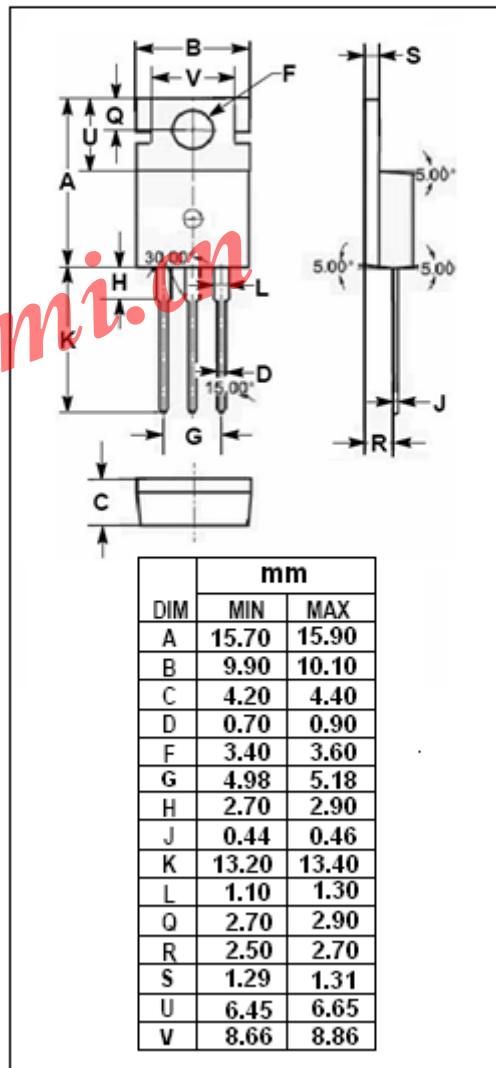
APPLICATIONS

- Designed for general-purpose amplifier and low-speed switching applications



ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	60	V
$V_{CEO}$	Collector-Emitter Voltage	60	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	4	A
$I_B$	Base Current	0.1	A
$P_C$	Collector Power Dissipation $T_C=25^\circ\text{C}$	50	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	2.5	$^\circ\text{C/W}$

## isc Silicon NPN Darlington Power Transistor

## MJE800T

## ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	60		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=1.5\text{A}; I_B=40\text{mA}$		2.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=40\text{mA}$		3.0	V
$V_{BE(on)-1}$	Base-Emitter On Voltage	$I_C=1.5\text{A}; V_{CE}=3\text{V}$		2.5	V
$V_{BE(on)-2}$	Base-Emitter On Voltage	$I_C=4\text{A}; V_{CE}=3\text{V}$		3.0	V
$I_{CEO}$	Collector Cutoff Current	$V_{CE}=60\text{V}; I_B=0$		0.1	mA
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=60\text{V}; I_E=0$ $V_{CB}=60\text{V}; I_E=0; T_C=100^\circ\text{C}$		0.1 0.5	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$		2.0	mA
$h_{FE-1}$	DC Current Gain	$I_C=1.5\text{A}; V_{CE}=3\text{V}$	750		
$h_{FE-2}$	DC Current Gain	$I_C=4\text{A}; V_{CE}=3\text{V}$	100		